

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> MAX        | I <sub>D</sub> MAX<br>T <sub>C</sub> = +25°C |
|-------------------|--------------------------------|--|
| -40V              | 10mΩ @ V <sub>GS</sub> = -10V  | -76A   |
|                   | 14mΩ @ V <sub>GS</sub> = -4.5V | -58A   |

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

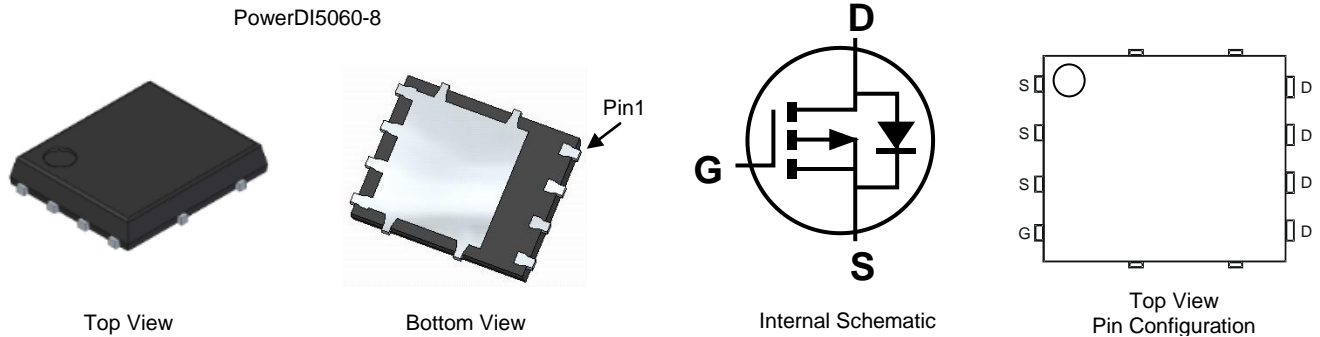
- DC-DC Converters
- Power Management Functions
- Analog Switch

## Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Complaint Part is Available Under Separate Datasheet ([DMP4011SPSQ](#))**

## Mechanical Data

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

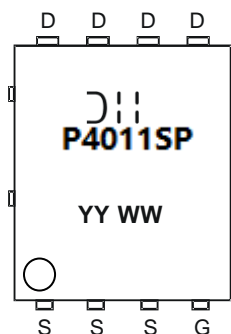


## Ordering Information (Note 4)

| Part Number   | Case          | Packaging          |
|---------------|---------------|--------------------|
| DMP4011SPS-13 | PowerDI5060-8 | 2500 / Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



☺☺☺ = Manufacturer's Marking  
 P4011SP = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 19 = 2019)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   |              | Symbol                 | Value | Unit |
|--|--------------|------------------------|-------|------|
| Drain-Source Voltage                                     |              | V <sub>DSS</sub>       | -40   | V    |
| Gate-Source Voltage                                      |              | V <sub>GSS</sub>       | ±20   | V    |
| Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V | Steady State | T <sub>C</sub> = +25°C | -76   | A    |
|  |              | T <sub>C</sub> = +70°C | -61   |      |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V | Steady State | T <sub>A</sub> = +25°C | -11.7 | A    |
|  |              | T <sub>A</sub> = +70°C | -9.4  |      |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)       |              | I <sub>DM</sub>        | -300  | A    |
| Maximum Body Diode Continuous Current (Note 6)           |              | I <sub>S</sub>         | -8.9  | A    |
| Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)      |              | I <sub>SM</sub>        | -300  | A    |
| Avalanche Current (Note 8) L = 1mH                       |              | I <sub>AS</sub>        | -22   | A    |
| Avalanche Energy (Note 8) L = 1mH                        |              | E <sub>AS</sub>        | 250   | mJ   |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   |                        | Symbol                            | Value       | Unit |
|--|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 1.3         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State           | R <sub>θJA</sub>                  | 96.4        | °C/W |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 2.3         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State           | R <sub>θJA</sub>                  | 55          | °C/W |
| Thermal Resistance, Junction to Case (Note 7)    |                        | R <sub>θJC</sub>                  | 1.3         | °C/W |
| Operating and Storage Temperature Range          |                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                              | Symbol              | Min  | Typ  | Max  | Unit | Test Condition   |
|---|---------------------|------|------|------|------|--|
| <b>OFF CHARACTERISTICS (Note 9)</b>         |                     |      |      |      |      |  |
| Drain-Source Breakdown Voltage              | BV <sub>DSS</sub>   | -40  | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA  |
| Zero Gate Voltage Drain Current             | I <sub>DSS</sub>    | —    | —    | -1   | µA   | V <sub>DS</sub> = -32V, V <sub>GS</sub> = 0V   |
| Gate-Source Leakage                         | I <sub>GSS</sub>    | —    | —    | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 9)</b>          |                     |      |      |      |      |  |
| Gate Threshold Voltage                      | V <sub>GS(TH)</sub> | -1.0 | -2.0 | -2.5 | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA                                  |
| Static Drain-Source On-Resistance           | R <sub>DS(ON)</sub> | —    | 6    | 10   | mΩ   | V <sub>GS</sub> = -10V, I <sub>D</sub> = -9.8A   |
|   |                     | —    | 10   | 14   |      | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -9.8A  |
| Diode Forward Voltage                       | V <sub>SD</sub>     | —    | -0.7 | -1   | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A   |
| <b>DYNAMIC CHARACTERISTICS (Note 10)</b>    |                     |      |      |      |      |  |
| Input Capacitance                           | C <sub>ISS</sub>    | —    | 2747 | —    | pF   | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V<br>f = 1MHz                                     |
| Output Capacitance                          | C <sub>OSS</sub>    | —    | 508  | —    |      |  |
| Reverse Transfer Capacitance                | C <sub>RSS</sub>    | —    | 222  | —    |      |  |
| Gate Resistance                             | R <sub>g</sub>      | —    | 21.4 | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz   |
| Total Gate Charge (V <sub>GS</sub> = -4.5V) | Q <sub>g</sub>      | —    | 25   | —    | nC   | V <sub>DS</sub> = -20V<br>I <sub>D</sub> = -9.8A   |
| Total Gate Charge (V <sub>GS</sub> = -10V)  | Q <sub>g</sub>      | —    | 52   | —    |      |  |
| Gate-Source Charge                          | Q <sub>gs</sub>     | —    | 8.5  | —    |      |  |
| Gate-Drain Charge                           | Q <sub>gd</sub>     | —    | 11.8 | —    |      |  |
| Turn-On Delay Time                          | t <sub>D(ON)</sub>  | —    | 6.6  | —    | ns   | V <sub>GS</sub> = -10V, V <sub>DD</sub> = -20V,<br>R <sub>g</sub> = 6Ω, I <sub>D</sub> = -1A |
| Turn-On Rise Time                           | t <sub>r</sub>      | —    | 6.5  | —    |      |  |
| Turn-Off Delay Time                         | t <sub>D(OFF)</sub> | —    | 222  | —    |      |  |
| Turn-Off Fall Time                          | t <sub>f</sub>      | —    | 138  | —    |      |  |
| Reverse Recovery Time                       | t <sub>RR</sub>     | —    | 25   | —    | ns   | I <sub>F</sub> = -9.8A, di/dt = -100A/µs   |
| Reverse Recovery Charge                     | Q <sub>RR</sub>     | —    | 17   | —    | nC   | I <sub>F</sub> = -9.8A, di/dt = -100A/µs   |

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.

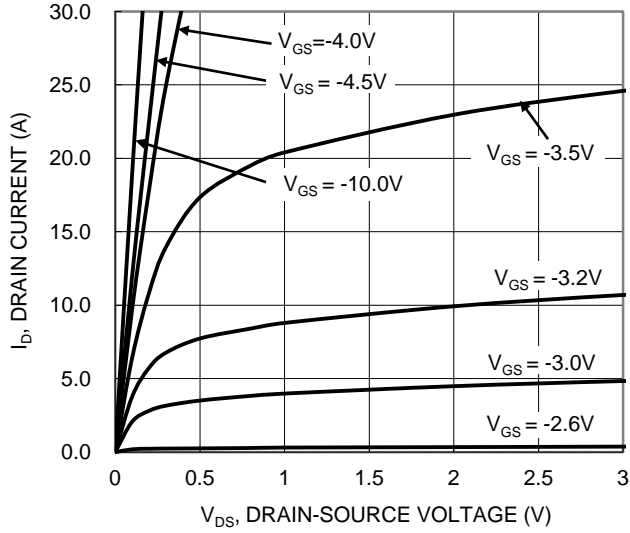


Figure 1. Typical Output Characteristic

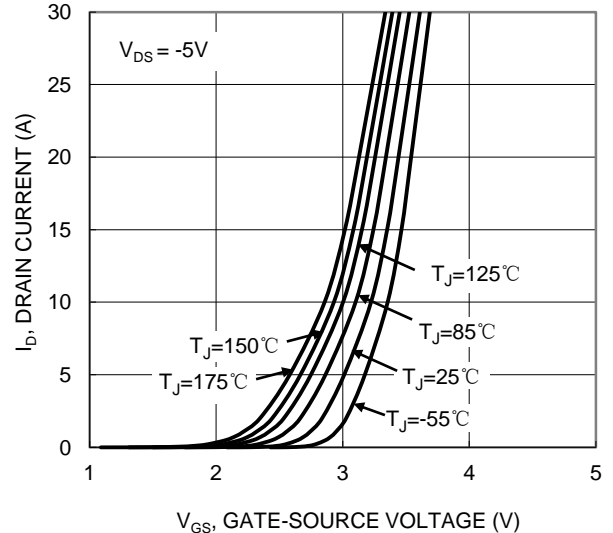


Figure 2. Typical Transfer Characteristic

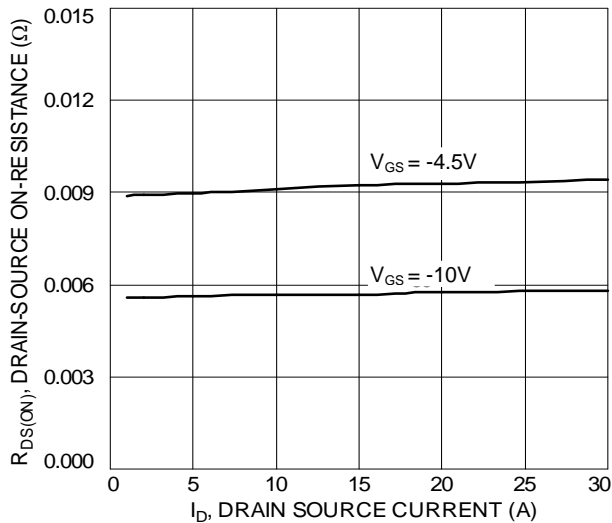


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

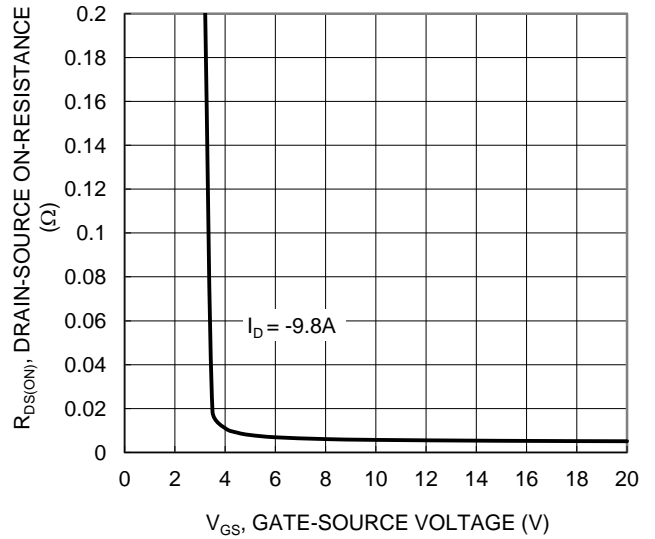


Figure 4. Typical Transfer Characteristic

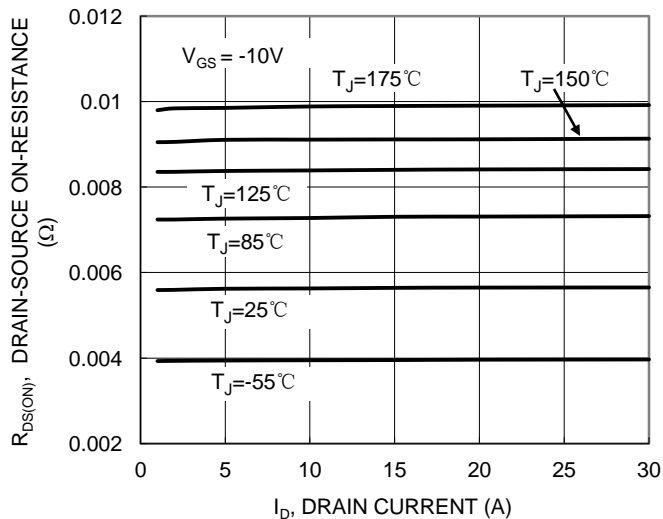


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

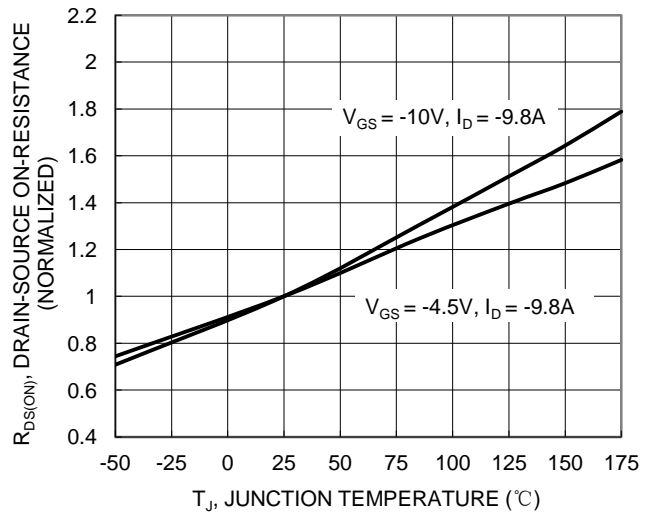
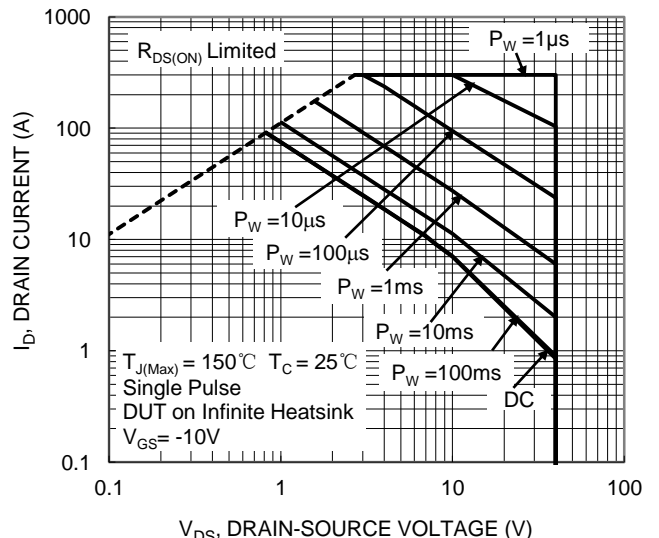
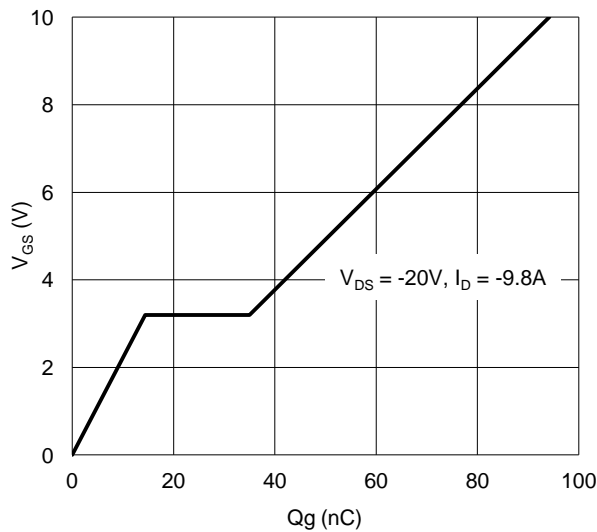
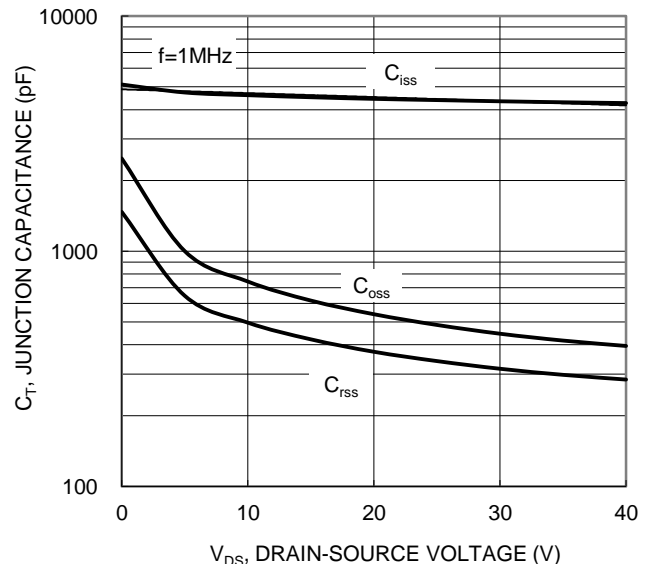
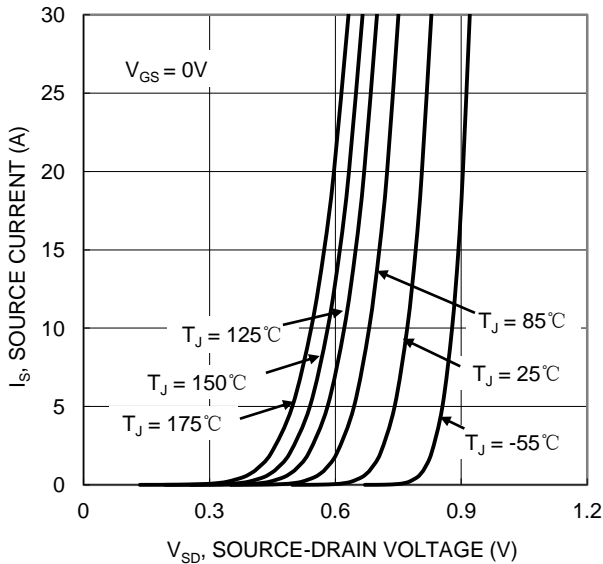
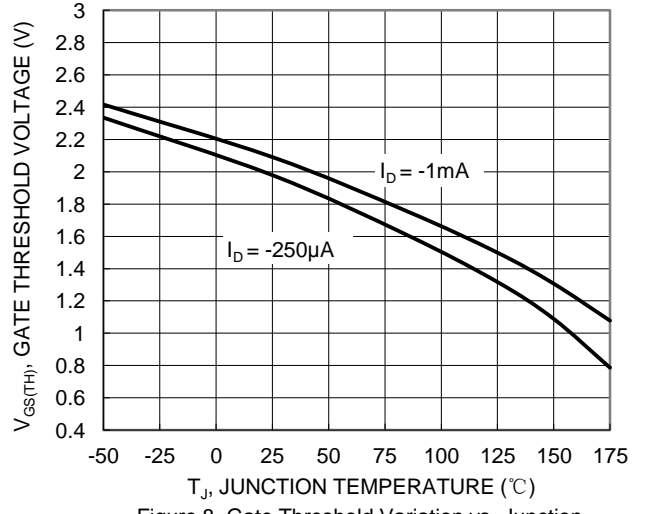
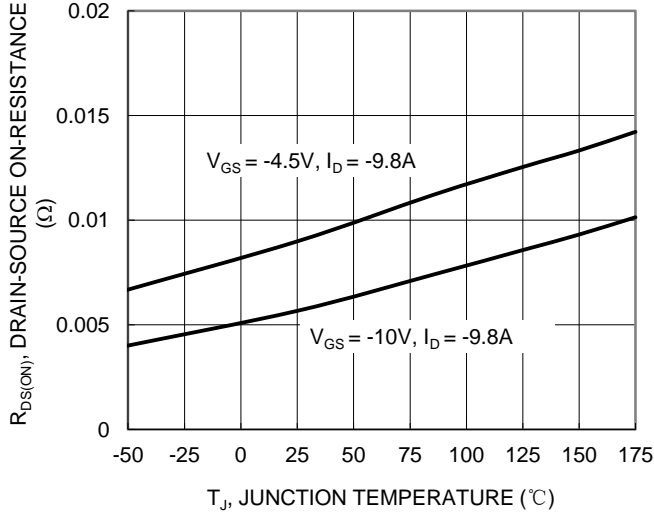


Figure 6. On-Resistance Variation with Temperature



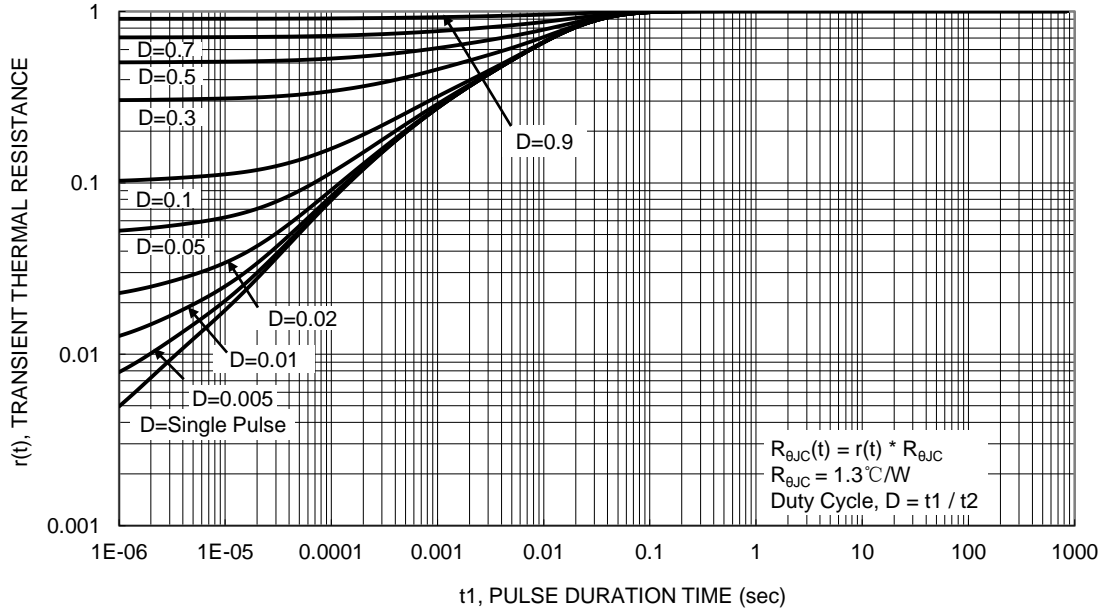
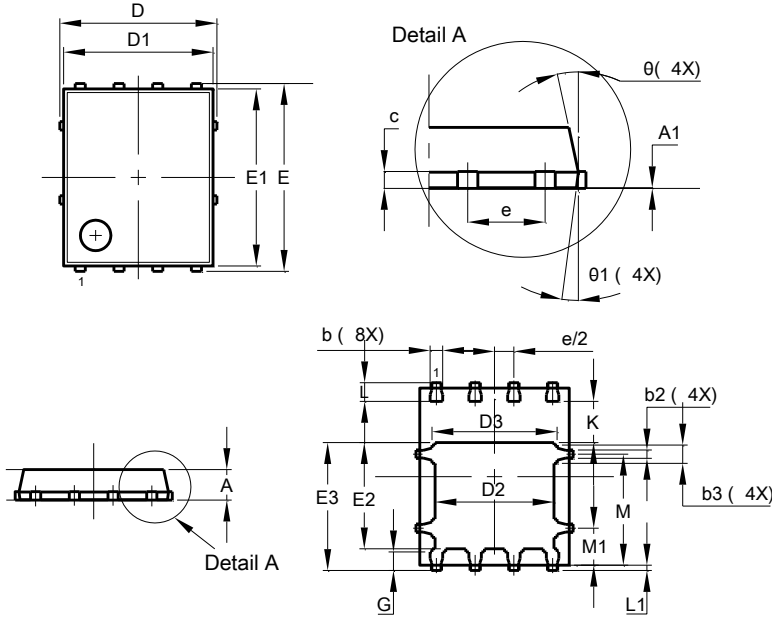


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**

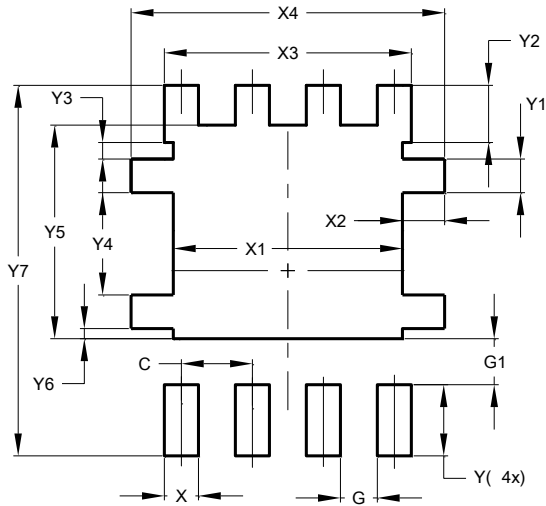


| PowerDI5060-8        |          |       |       |
|----------------------|----------|-------|-------|
| Dim                  | Min      | Max   | Typ   |
| A                    | 0.90     | 1.10  | 1.00  |
| A1                   | 0.00     | 0.05  | —     |
| b                    | 0.33     | 0.51  | 0.41  |
| b2                   | 0.200    | 0.350 | 0.273 |
| b3                   | 0.40     | 0.80  | 0.60  |
| c                    | 0.230    | 0.330 | 0.277 |
| D                    | 5.15 BSC |       |       |
| D1                   | 4.70     | 5.10  | 4.90  |
| D2                   | 3.70     | 4.10  | 3.90  |
| D3                   | 3.90     | 4.30  | 4.10  |
| E                    | 6.15 BSC |       |       |
| E1                   | 5.60     | 6.00  | 5.80  |
| E2                   | 3.28     | 3.68  | 3.48  |
| E3                   | 3.99     | 4.39  | 4.19  |
| e                    | 1.27 BSC |       |       |
| G                    | 0.51     | 0.71  | 0.61  |
| K                    | 0.51     | —     | —     |
| L                    | 0.51     | 0.71  | 0.61  |
| L1                   | 0.100    | 0.200 | 0.175 |
| M                    | 3.235    | 4.035 | 3.635 |
| M1                   | 1.00     | 1.40  | 1.21  |
| θ                    | 10°      | 12°   | 11°   |
| θ1                   | 6°       | 8°    | 7°    |
| All Dimensions in mm |          |       |       |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 1.270         |
| G          | 0.660         |
| G1         | 0.820         |
| X          | 0.610         |
| X1         | 4.100         |
| X2         | 0.755         |
| X3         | 4.420         |
| X4         | 5.610         |
| Y          | 1.270         |
| Y1         | 0.600         |
| Y2         | 1.020         |
| Y3         | 0.295         |
| Y4         | 1.825         |
| Y5         | 3.810         |
| Y6         | 0.180         |
| Y7         | 6.610         |

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